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Kind regards,

Team Nexperia



Ultra low capacitance bidirectional double ESD protection array

Rev. 01 — 14 August 2008

Product data sheet

1. Product profile

1.1 General description

Ultra low capacitance bidirectional double ElectroStatic Discharge (ESD) protection diode array in a SOT883 (SC-101) leadless ultra small Surface-Mounted Device (SMD) plastic package designed to protect up to two signal lines from the damage caused by ESD and other transients.

1.2 Features

Bidirectional ESD protection of up to two lines
 Ultra low diode capacitance: C_d = 2.9 pF
 IEC 61000-4-2; level 4 (ESD)
 Ultra low leakage current: I_{RM} = 5 nA
 AEC-Q101 qualified

1.3 Applications

- Computers and peripherals
 Audio and video equipment
 Cellular handsets and accessories
 10/100/1000 Mbit/s Ethernet
- Communication systems
- Portable electronics
- Subscriber Identity Module (SIM) card protection
- FireWire
- High-speed data lines

1.4 Quick reference data

Table 1.Quick reference data

```
T_{amb} = 25 \circ C unless otherwise specified.
```

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diode)					
V _{RWM}	reverse standoff voltage		-	-	5	V
C _d	diode capacitance	$f = 1 \text{ MHz}; V_R = 0 \text{ V}$	-	2.9	3.5	pF



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2. Pinning information

Table 2.	Pinning		
Pin	Description	Simplified outline	Graphic symbol
1	cathode (diode 1)		
2	cathode (diode 2)		
3	common cathode	2 Transparent top view	2

3. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
PESD5V0U2BM	SC-101	leadless ultra small plastic package; 3 solder lands; body $1.0 \times 0.6 \times 0.5$ mm	SOT883			

4. Marking

Table 4.	Marking codes	
Type num	ber	Marking code
PESD5V0	U2BM	GA

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per device					
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-55	+150	°C
T _{stg}	storage temperature		-65	+150	°C

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Table 6.ESD maximum ratings

 $T_{amb} = 25 \circ C$ unless otherwise specified.

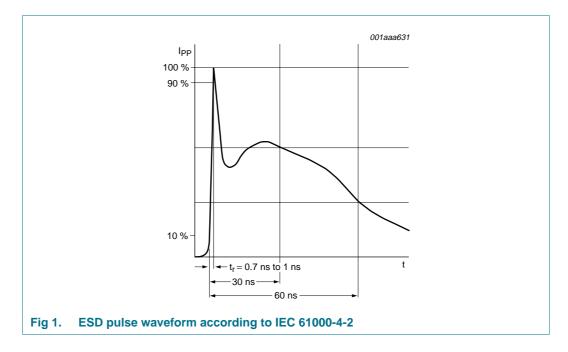
Symbol	Parameter	Conditions		Min	Max	Unit
Per diode)					
V _{ESD} electrostatic discharge voltage			[1][2]			
	IEC 61000-4-2 (contact discharge)		-	10	kV	
		MIL-STD-883 (human body model)		-	8	kV

[1] Device stressed with ten non-repetitive ESD pulses.

[2] Measured from pin 1 or 3 to pin 2 or 3.

Table 7. ESD standards compliance

Standard	Conditions
Per diode	
IEC 61000-4-2; level 4 (ESD)	> 15 kV (air); > 8 kV (contact)
MIL-STD-883; class 3 (human body model)	> 4 kV

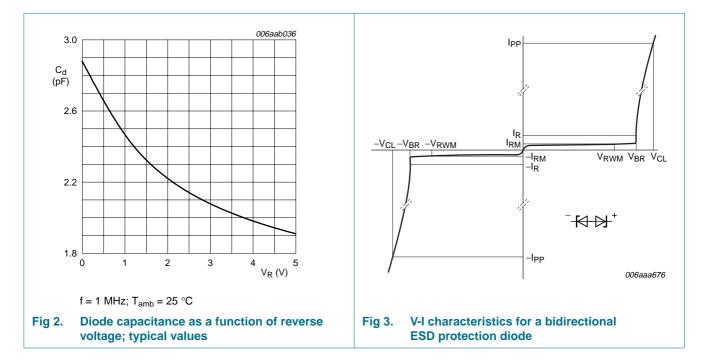


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6. Characteristics

 $T_{amb} = 25 \circ C$ unless otherwise specified.

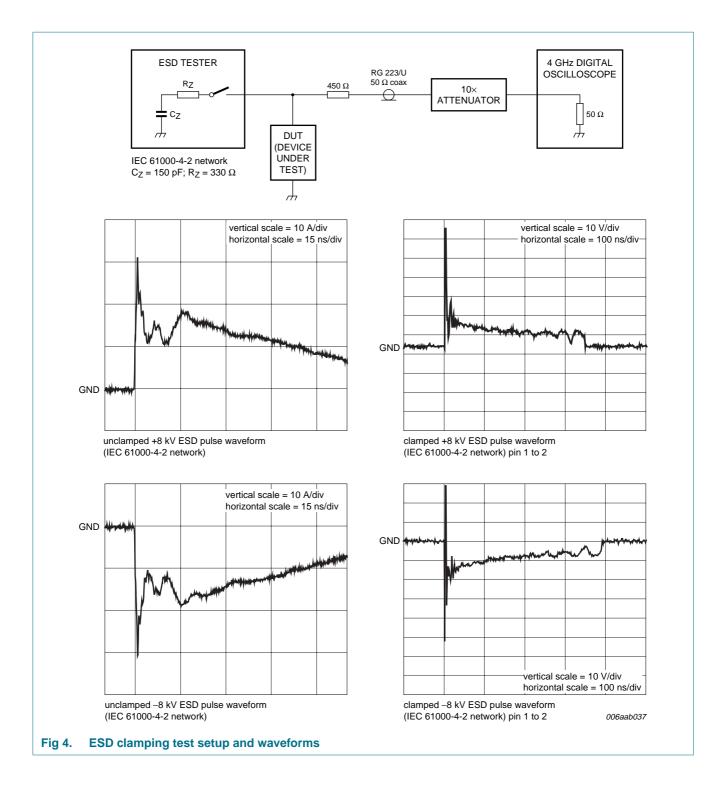
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diod	le					
V _{RWM}	reverse standoff voltage		-	-	5	V
I _{RM}	reverse leakage current	$V_{RWM} = 5 V$	-	5	100	nA
V_{BR}	breakdown voltage	$I_R = 5 \text{ mA}$	5.5	6.5	9.5	V
C _d	diode capacitance	f = 1 MHz				
		$V_R = 0 V$	-	2.9	3.5	pF
		$V_R = 5 V$	-	1.9	-	pF
r _{dif}	differential resistance	I _R = 1 mA	-	-	100	Ω



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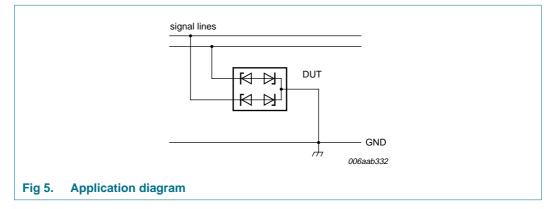


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7. Application information

The PESD5V0U2BM is designed for the protection of up to two bidirectional data or signal lines from the damage caused by ESD and surge pulses. The device may be used on lines where the signal polarities are both, positive and negative with respect to ground.



Circuit board layout and protection device placement

Circuit board layout is critical for the suppression of ESD, Electrical Fast Transient (EFT) and surge transients. The following guidelines are recommended:

- 1. Place the PESD5V0U2BM as close to the input terminal or connector as possible.
- 2. The path length between the PESD5V0U2BM and the protected line should be minimized.
- 3. Keep parallel signal paths to a minimum.
- 4. Avoid running protected conductors in parallel with unprotected conductors.
- Minimize all Printed-Circuit Board (PCB) conductive loops including power and ground loops.
- 6. Minimize the length of the transient return path to ground.
- 7. Avoid using shared transient return paths to a common ground point.
- 8. Ground planes should be used whenever possible. For multilayer PCBs, use ground vias.

8. Test information

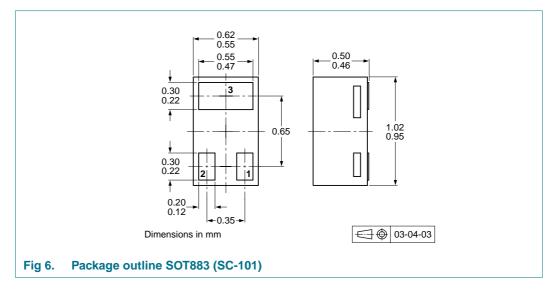
8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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9. Package outline



10. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

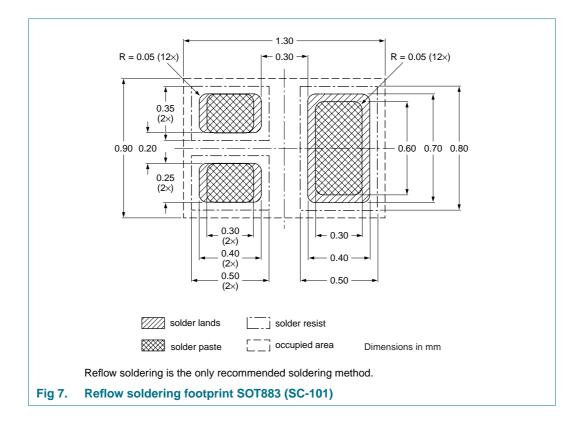
Type number	Package	Description	Packing quantity 10000
PESD5V0U2BM	SOT883	2 mm pitch, 8 mm tape and reel	-315

[1] For further information and the availability of packing methods, see <u>Section 14</u>.

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11. Soldering



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12. Revision history

Table 10. Revision hist	Revision history							
Document ID	Release date	Data sheet status	Change notice	Supersedes				
PESD5V0U2BM_1	20080814	Product data sheet	-	-				

13. Legal information

13.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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Product data sheet

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